

## 60V N-Channel Power MOSFE

### Description

The MDT50N06 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge. It can be used in a wide variety of applications.

### General Features

- ①  $V_{DS}=60V$ ,  $R_{DS(on)}<15m\Omega$  @  $V_{GS}=10V$ ,  $I_D=50A$  (Typ:11m $\Omega$ )
- ② High density cell design for lower  $R_{DS(on)}$
- ③ Fully characterized avalanche voltage and current
- ④ Good stability and uniformity with high EAS
- ⑤ Excellent package for good heat dissipation

### Application

- ① Power Switching application
- ② Hard switched and High frequency circuits
- ③ Uninterruptible power supply

### Package Marking And Ordering Information:

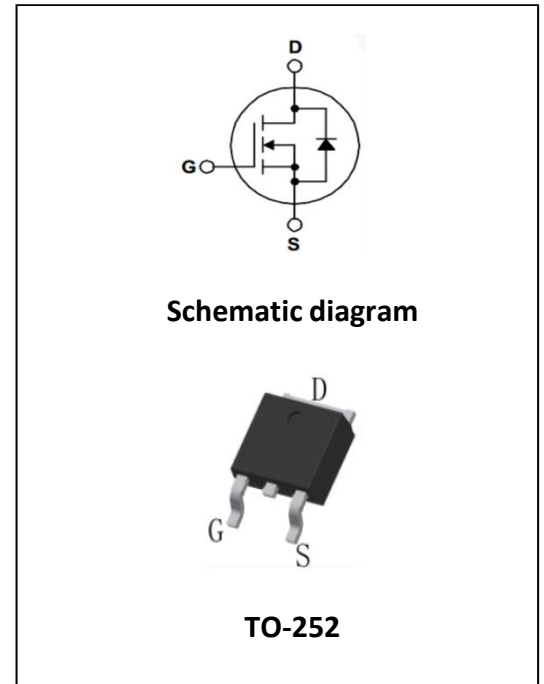
| Ordering Codes | Package | Product Code | Packing |
|----------------|---------|--------------|---------|
| MDT50N06-D     | TO-252  | MDT60N06     | Tube    |

### Electrical Characteristics @ $T_a=25^{\circ}C$ (unless otherwise specified)

| Parameter                                        | Symbol         | Limit      | Unit        |
|--------------------------------------------------|----------------|------------|-------------|
| Drain-Source Voltage                             | $V_{DS}$       | 60         | V           |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 20$   | V           |
| Drain Current-Continuous                         | $I_D$          | 50         | A           |
| Drain Current-Pulsed (Note 1)                    | $I_{DM}$       | 200        | A           |
| Maximum Power Dissipation( $T_c=25^{\circ}C$ )   | $P_D$          | 87         | W           |
| Single pulse avalanche energy (Note 2)           | $E_{AS}$       | 120        | mJ          |
| Operating Junction and Storage Temperature Range | $T_J, T_{STG}$ | -55 To 175 | $^{\circ}C$ |

### Thermal Characteristic

|                                     |                 |      |               |
|-------------------------------------|-----------------|------|---------------|
| Thermal Resistance,Junction-to-Case | $R_{\theta JC}$ | 1.72 | $^{\circ}C/W$ |
|-------------------------------------|-----------------|------|---------------|



**Electrical Characteristics (TA=25℃ unless otherwise noted)**

| Parameter                                            | Symbol              | Condition                                                                                | Min | Typ | Max  | Unit |
|------------------------------------------------------|---------------------|------------------------------------------------------------------------------------------|-----|-----|------|------|
| Off Characteristics                                  |                     |                                                                                          |     |     |      |      |
| Drain-Source Breakdown Voltage                       | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =250μA                                                | 60  | -   | -    | V    |
| Zero Gate Voltage Drain Current                      | I <sub>DSS</sub>    | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V                                                | -   | -   | 1    | μA   |
| Gate-Body Leakage Current                            | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                                               | -   | -   | ±100 | nA   |
| On Characteristics                                   |                     |                                                                                          |     |     |      |      |
| Gate Threshold Voltage                               | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                                 | 2   | 3   | 4    | V    |
| Drain-Source On-State Resistance <sup>(Note 3)</sup> | R <sub>DS(ON)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =25A                                                | -   | 11  | 15   | mΩ   |
| Forward Transconductance                             | g <sub>FS</sub>     | V <sub>DS</sub> =25V, I <sub>D</sub> =25A                                                | -   | 25  | -    | S    |
| Dynamic Characteristics                              |                     |                                                                                          |     |     |      |      |
| Input Capacitance                                    | C <sub>iss</sub>    | V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,<br>f=1.0MHz                                   | -   | 910 | -    | pF   |
| Output Capacitance                                   | C <sub>oss</sub>    |                                                                                          | -   | 100 | -    | pF   |
| Reverse Transfer Capacitance                         | C <sub>rss</sub>    |                                                                                          | -   | 30  | -    | pF   |
| Switching Characteristics <sup>(Note 4)</sup>        |                     |                                                                                          |     |     |      |      |
| Turn-on Delay Time                                   | t <sub>d(on)</sub>  | V <sub>DD</sub> =30V, I <sub>D</sub> =20A,<br>V <sub>GS</sub> =10V, R <sub>GEN</sub> =5Ω | -   | 26  | -    | nS   |
| Turn-on Rise Time                                    | t <sub>r</sub>      |                                                                                          | -   | 6   | -    | nS   |
| Turn-Off Delay Time                                  | t <sub>d(off)</sub> |                                                                                          | -   | 52  | -    | nS   |
| Turn-Off Fall Time                                   | t <sub>f</sub>      |                                                                                          |     | 7   | -    | nS   |
| Total Gate Charge                                    | Q <sub>g</sub>      | V <sub>DS</sub> =30V, I <sub>D</sub> =50A<br>V <sub>GS</sub> =10V                        | -   | 31  | -    | nC   |
| Gate-Source Charge                                   | Q <sub>gs</sub>     |                                                                                          | -   | 9   | -    | nC   |
| Gate-Drain Charge                                    | Q <sub>gd</sub>     |                                                                                          | -   | 5   | -    | nC   |
| Drain-Source Diode Characteristics                   |                     |                                                                                          |     |     |      |      |
| Diode Forward Voltage                                | V <sub>SD</sub>     | V <sub>GS</sub> =0V, I <sub>S</sub> =50A                                                 | -   | -   | 1.2  | V    |

**Notes:**

Repetitive Rating: Pulse width limited by maximum junction temperature.

EAS condition :T j=25℃,VDD=30V,VGS=10V,L=0.5mH,Rg=25Ω

Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

Guaranteed by design, not subject to production.

## Characteristics Curves

Figure 1 Output Characteristics

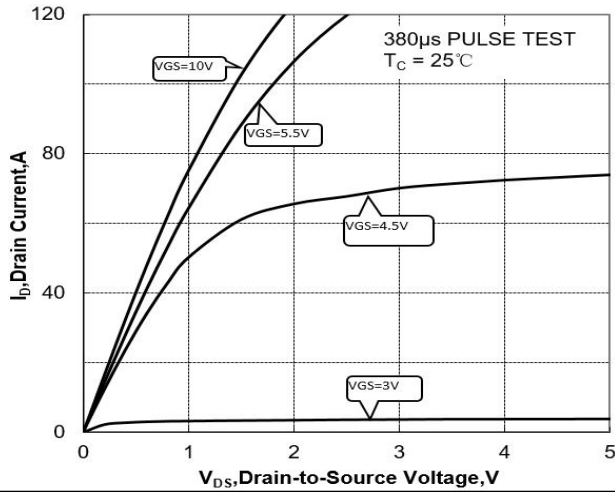


Figure 2 Transfer Characteristics

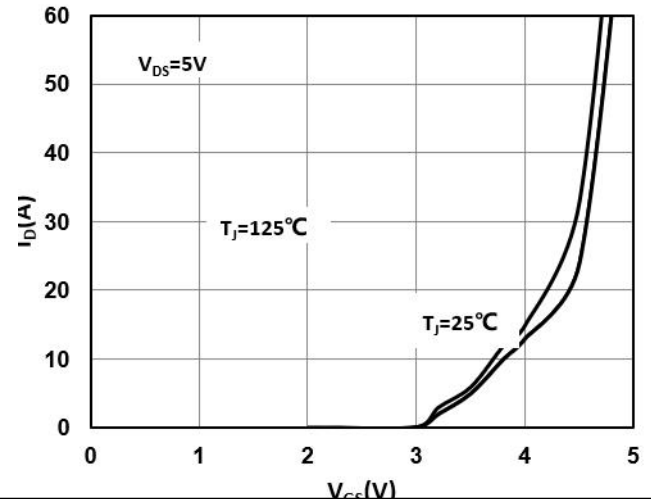


Figure 3 On-Resistance vs.  $I_D$  and  $V_{GS}$

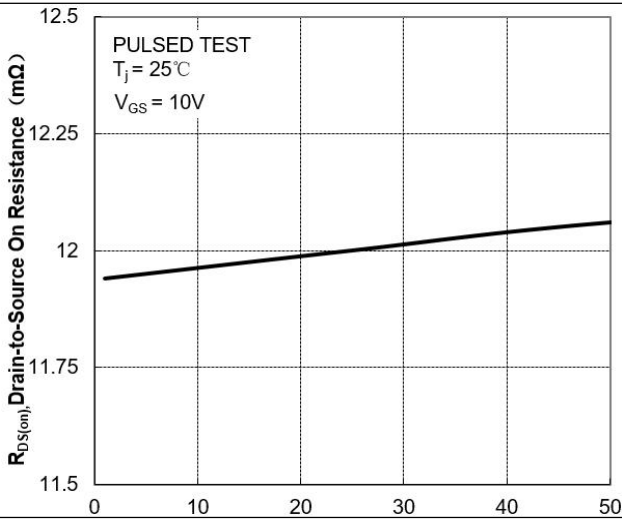


Figure 4 On-Resistance vs. Junction Temperature

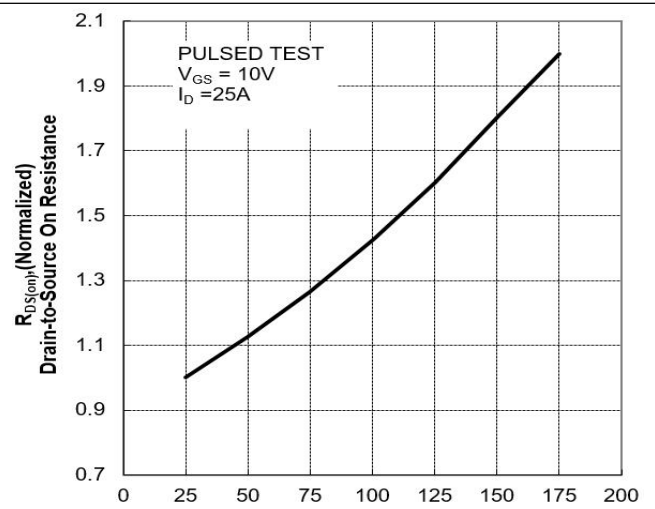


Figure 5 On-Resistance vs.  $V_{GS}$

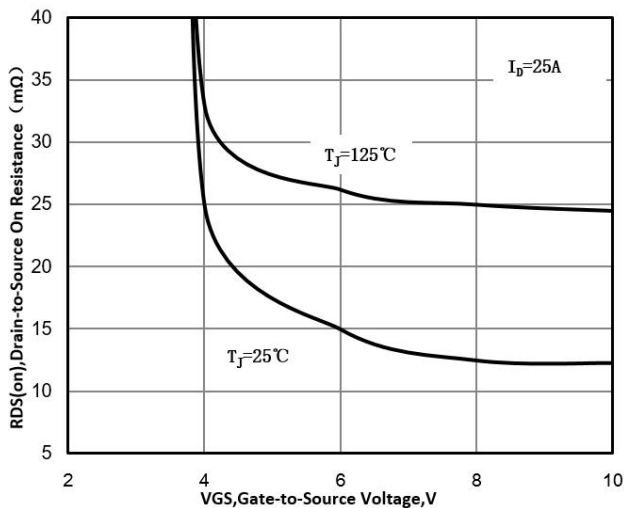


Figure 6 Body Diode Forward Voltage

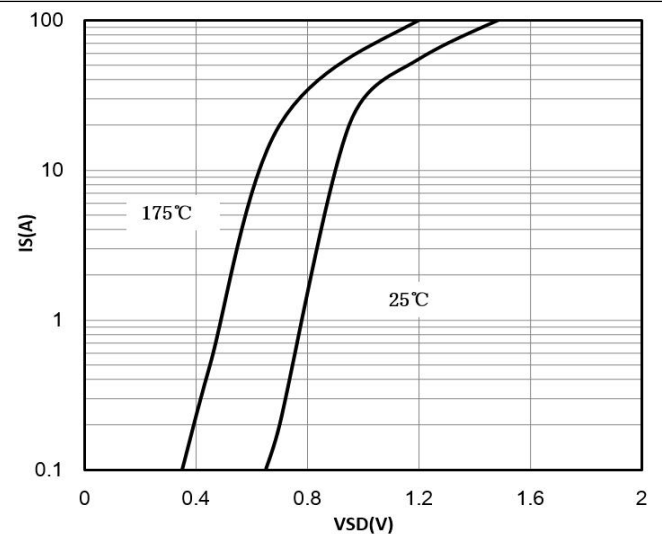


Figure 7 Gate-Charge Characteristics

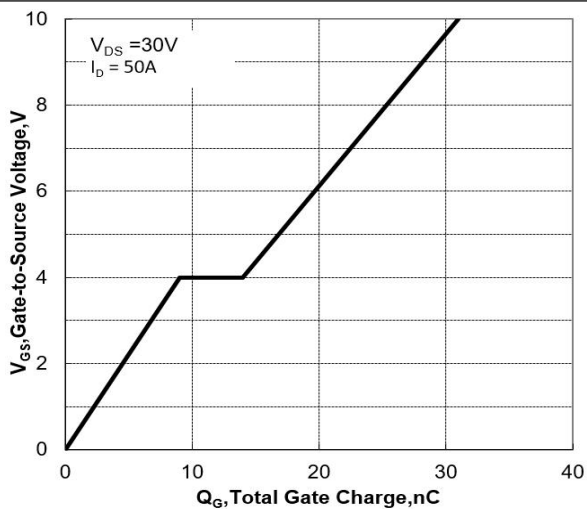


Figure 8 Capacitance Characteristics

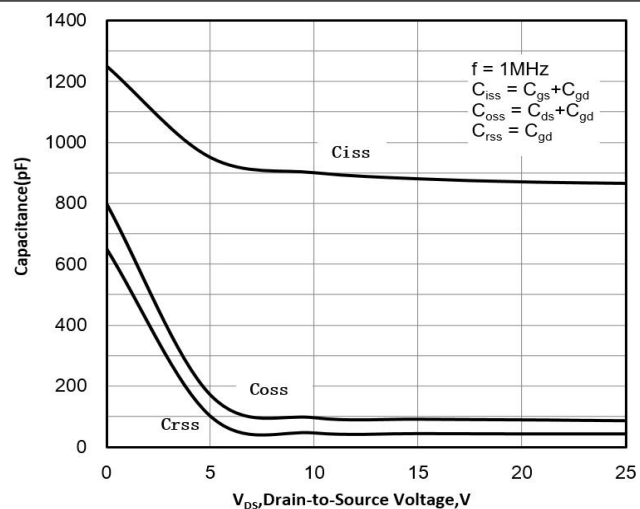


Figure 9 Maximum Forward Biased Safe Operation Area

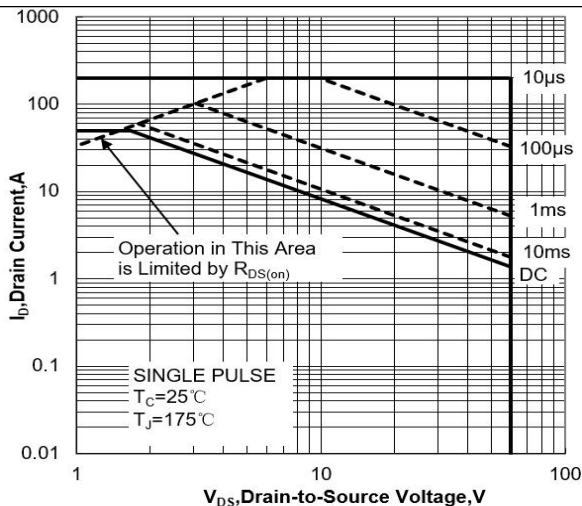


Figure 10 Single Pulse Power Rating Junction-to-Ambient

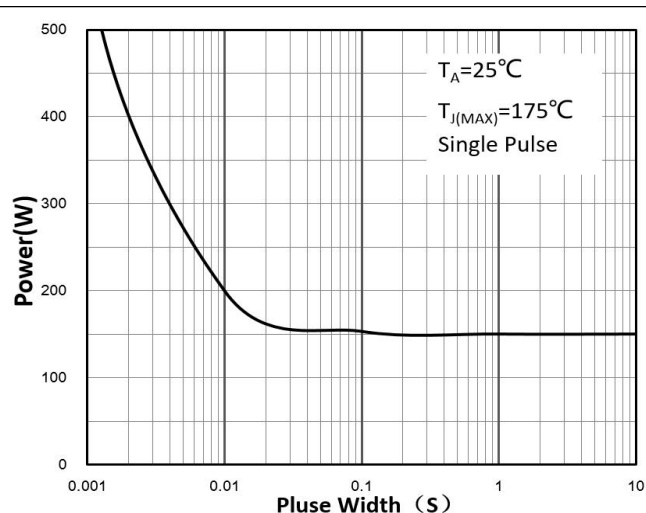
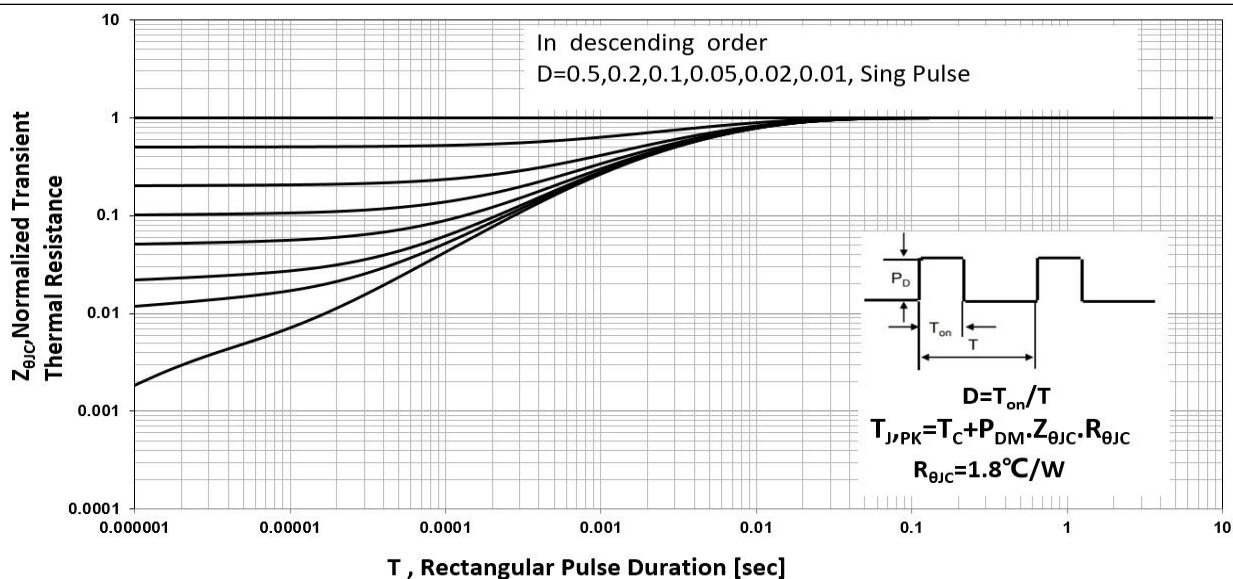
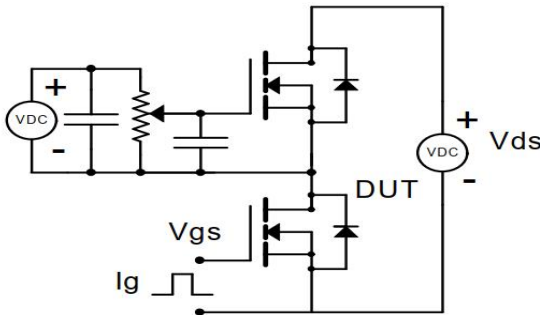
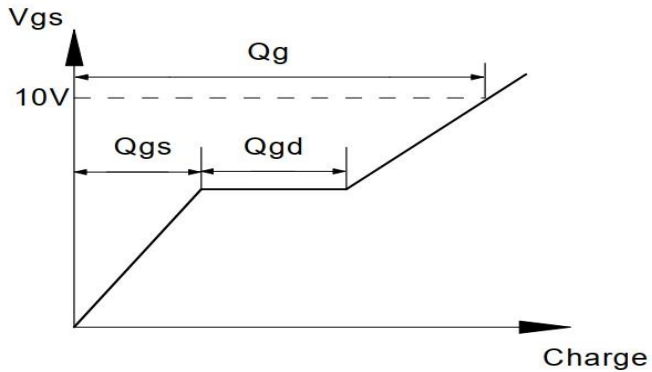
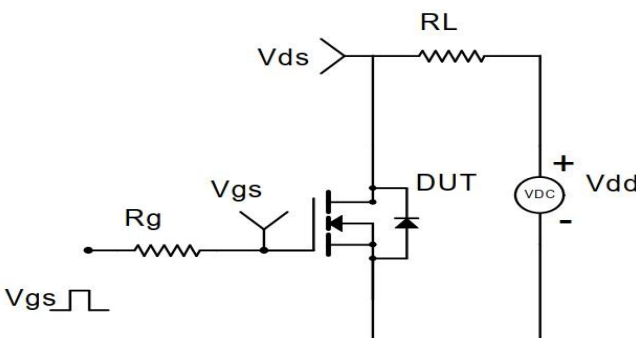
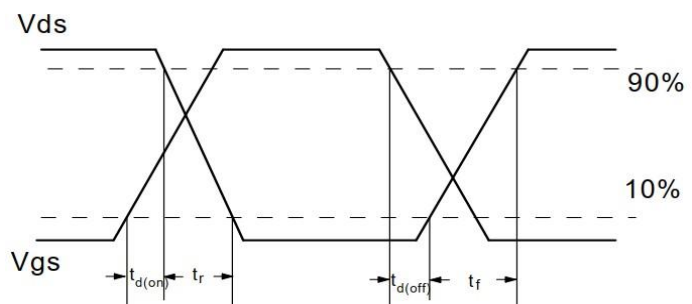
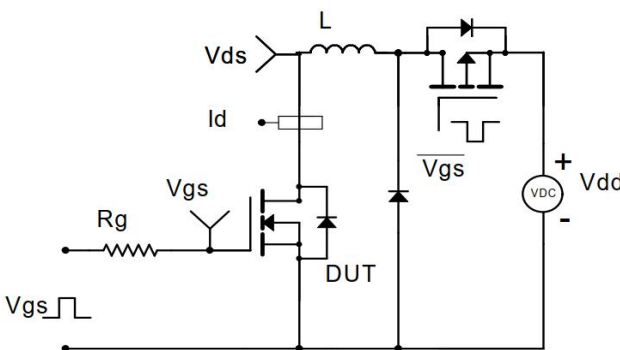
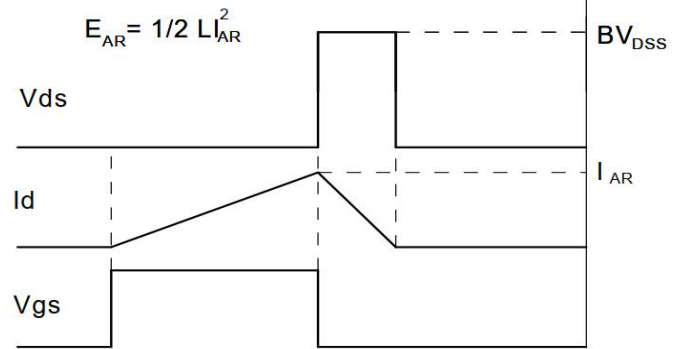
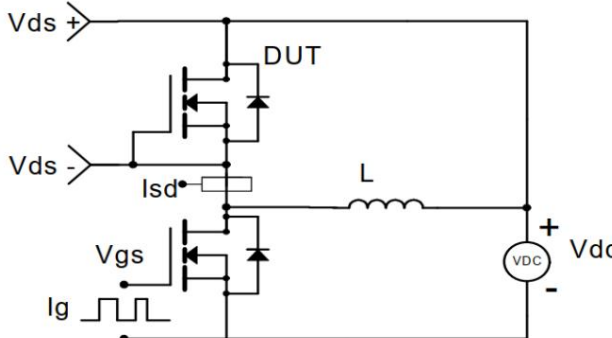
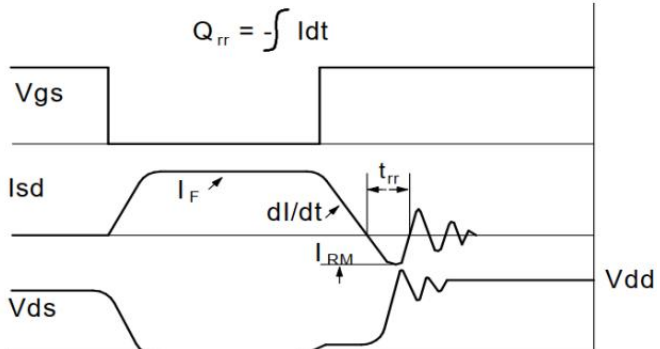


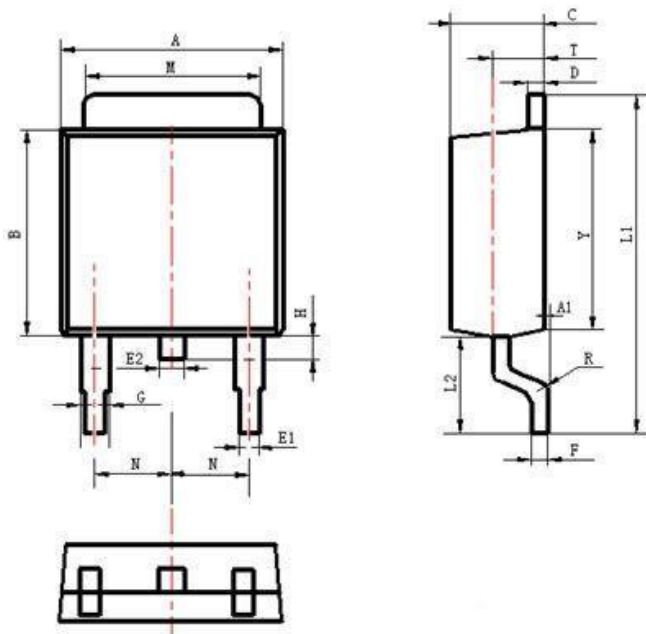
Figure 11 Normalized Maximum Transient Thermal Impedance



## Test Circuit and Waveform

| Gate Charge Test Circuit                                                            | Gate Charge Test Waveform                                                            |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|    |    |
| Resistive Switching Test Circuit                                                    | Resistive Switching Test Waveforms                                                   |
|   |   |
| Unclamped Inductive Switching (UIS) Test Circuit                                    | Unclamped Inductive Switching (UIS) Test Waveforms                                   |
|   |  |
| Diode Recovery Test Circuit                                                         | Diode Recovery Test Waveforms                                                        |
|  |  |

## Package Description



| Items | Values (mm) |       |
|-------|-------------|-------|
|       | MIN         | MAX   |
| A     | 6.30        | 6.90  |
| A1    | 0           | 0.13  |
| B     | 5.70        | 6.30  |
| C     | 2.10        | 2.50  |
| D     | 0.30        | 0.60  |
| E1    | 0.60        | 0.90  |
| E2    | 0.70        | 1.00  |
| F     | 0.30        | 0.60  |
| G     | 0.70        | 1.20  |
| L1    | 9.60        | 10.50 |
| L2    | 2.70        | 3.10  |
| H     | 0.60        | 1.00  |
| M     | 5.10        | 5.50  |
| N     | 2.09        | 2.49  |
| R     | 0.3         |       |
| T     | 1.40        | 1.60  |
| Y     | 5.10        | 6.30  |

TO-252 Package



迈诺斯科技

MDT50N06

**NOTE:**

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

**CONTACT:**

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